



NPN Epitaxial Planar Silicon Transistor

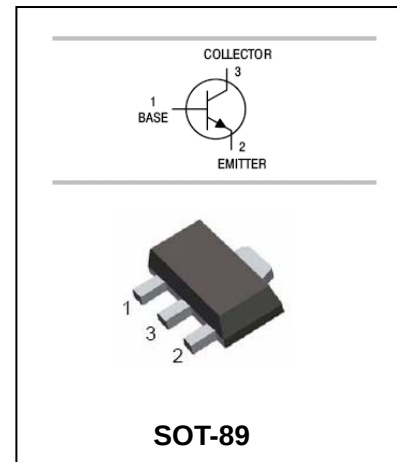
2SC4272

FEATURES

- Small size making it easy to provide high-density, small-sized hybrid IC's.



Lead-free



ORDERING INFORMATION

Type No.	Marking	Package Code
2SC4272	CH	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	75	V
V _{CEO}	Collector-Emitter Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	1.0	A
I _{CP}	Collector Current(Pulse)	1.5	A
P _C	Collector Dissipation	1.3	W
T _j , T _{stg}	Junction and Storage Temperature	-55 to +150	°C



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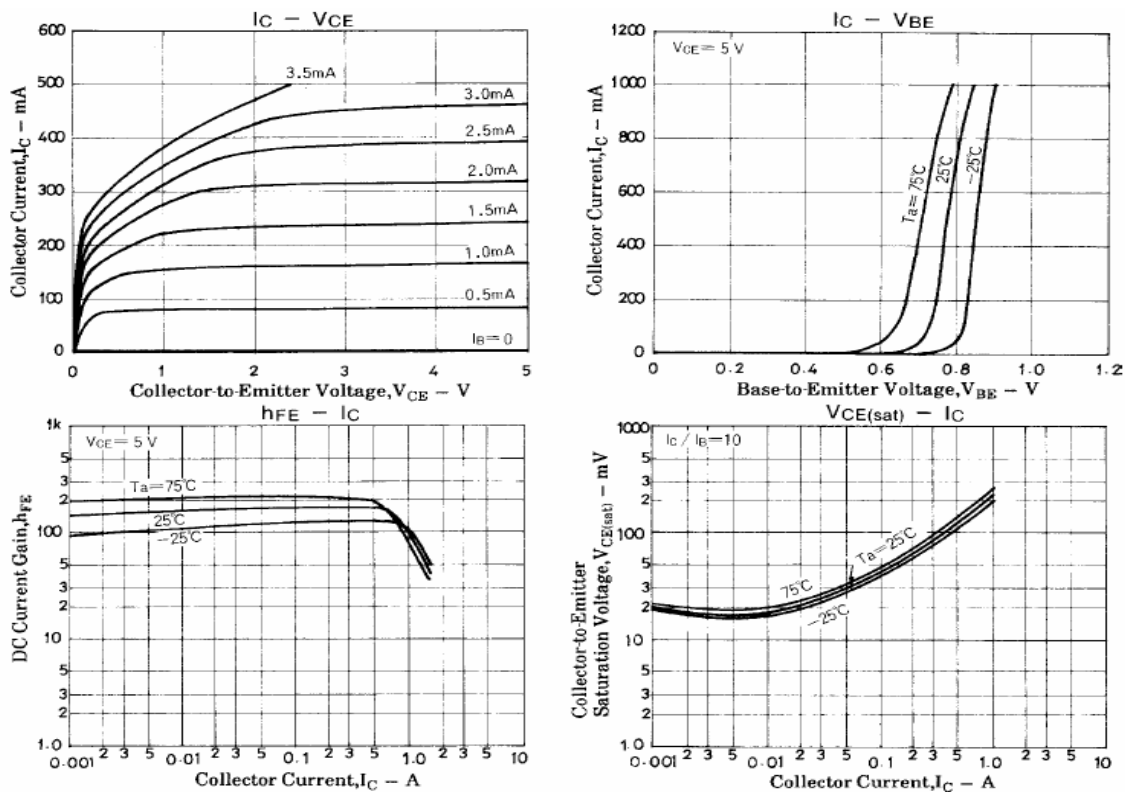
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	75			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			1.0	μA
DC current gain	h_{FE}	$V_{CE}=5V, I_C=500mA$	60		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=0.5A, I_B=0.05A$		0.2	0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=0.5A, I_B=0.05A$		0.9	1.2	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA$	180	250		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		15		pF

CLASSIFICATION OF h_{FE}

Rank	60-120	100-200	160-320
Range	D	E	F

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



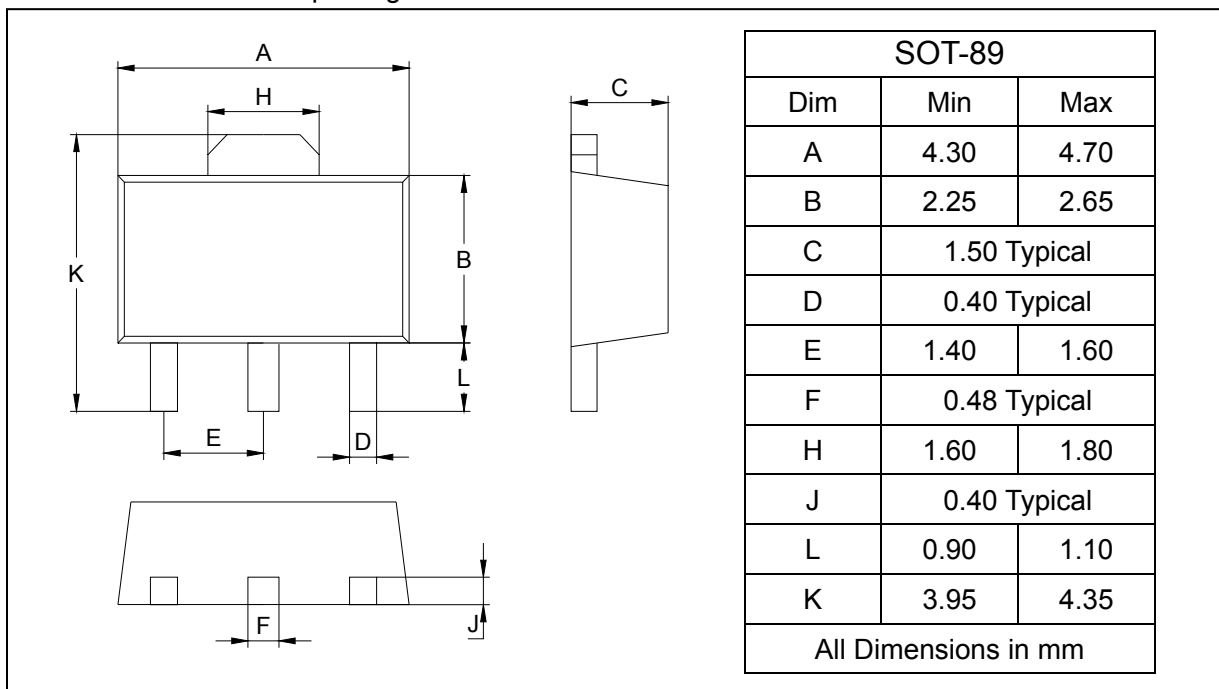
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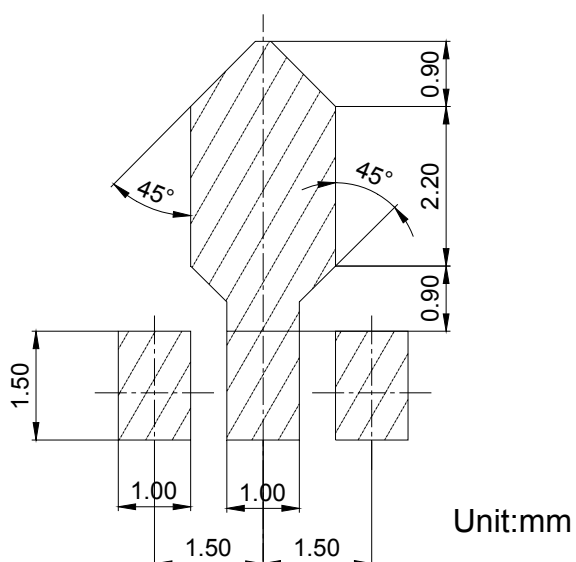
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC4272	SOT-89	1000/Tape&Reel